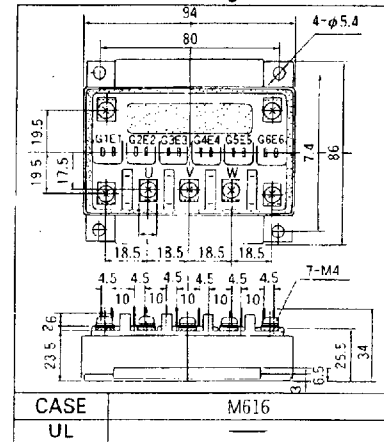


IGBT MODULE (L series)
■ Features

- High Speed Switching
- Low Saturation Voltage
- Voltage Drive

■ Applications

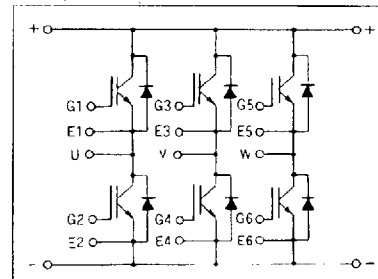
- Inverter for Motor Drive
- AC and DC Servo Drive Amplifier
- Uninterruptible Power Supply
- Industrial Machines, such as Welding Machines

■ Outline Drawings

■ Maximum Ratings and Characteristics
● Absolute Maximum Ratings

Items	Symbols	Ratings	Units
Collector-Emitter Voltage	V_{CES}	600	V
Gate-Emitter Voltage	V_{GES}	± 20	V
Collector Current	Continuous	I_C	75
	1ms	$I_C \text{ pulse}$	150
	Continuous	$-I_C$	75
	1ms	$-I_C \text{ pulse}$	150
Max. Power Dissipation	P_C	325	W
Operating Temperature	T_j	$+150$	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	$-40 \text{ to } +125$	$^{\circ}\text{C}$
Net. Weight		510	g
Isolation Voltage	AC, 1min.	V_{scl}	2500
Screw Torque	Mounting *1	35	$\text{kg}\cdot\text{cm}$
	Terminals *2	17	

*1 Recommendable Value: 25 to 35 $\text{kg}\cdot\text{cm}$ (M5)

*2 Recommendable Value: 13 to 17 $\text{kg}\cdot\text{cm}$ (M4)

■ Equivalalent Circuit Schematic

● Electrical Characteristics ($T_j=25^{\circ}\text{C}$)

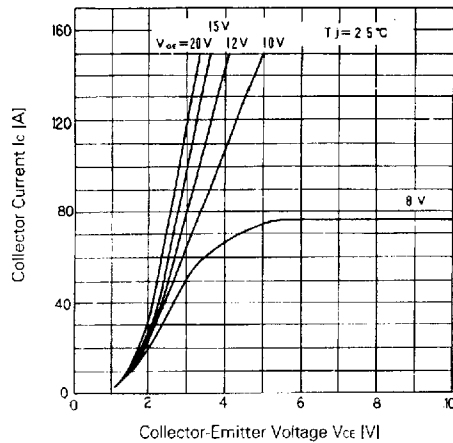
Items	Symbols	Test Conditions	Min.	Typ.	Max.	Units
Zero Gate Voltage Collector Current	I_{CES}	$V_{GE}=0V$ $V_{CE}=600V$ $T_j=25^{\circ}\text{C}$			1.0	mA
Gate-Emitter Leakage Current	I_{GES}	$V_{CE}=0V$ $V_{GE}=\pm 20V$			100	nA
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$V_{CE}=20V$ $I_C=75mA$	3.0		6.0	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$V_{GE}=15V$ $I_C=75A$		2.7	3.5	V
Input Capacitance	C_{ies}	$V_{GE}=0V$		7100		pF
Output Capacitance	C_{oes}	$V_{CE}=10V$		-		pF
Reverse Transfer Capacitance	C_{res}	$f=1\text{MHz}$		-		pF
Turn-on Time *3	t_{on}	$V_{CC}=300V$		0.4	0.8	μs
	t_r	$I_C=75A$		0.3	0.6	
	t_{off}	$V_{GE}=\pm 15V$		0.6	1.0	
Turn-off Time *4	t_i	$R_g=33\Omega$		0.2	0.35	μs
Diode Forward On-Voltage	V_F	$I_F=75A$ $V_{GE}=0V$			2.5	V
Reverse Recovery Time	t_r	$I_F=75A$ $-di/dt=225A/\mu\text{s}$ $V_{GE}=-10V$			300	ns

*3 Resistive load

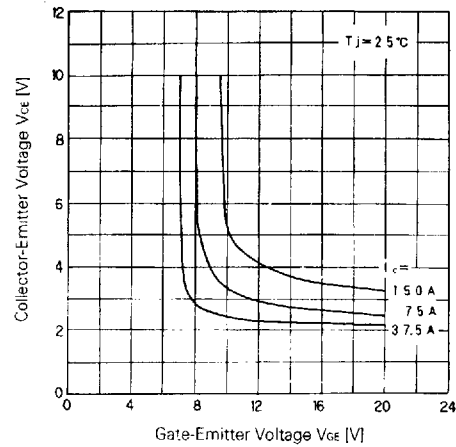
*4 Inductive load

● Thermal Characteristics

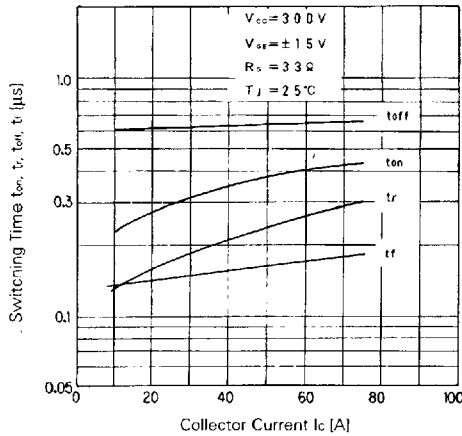
Items	Symbols	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance	$R_{th(j-c)}$	IGBT			0.385	$^{\circ}\text{C/W}$
	$R_{th(j-d)}$	Diode			0.35	
	$R_{th(c-l)}$	With Thermal compound		0.05		



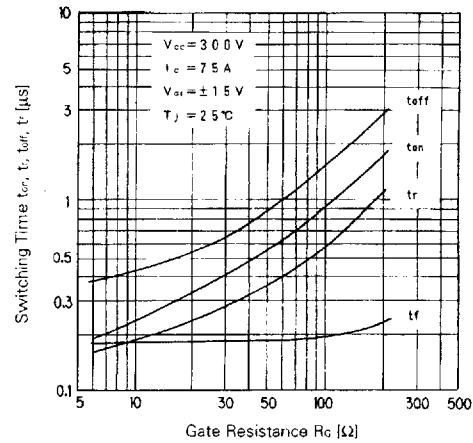
Collector Current vs. Collector-Emitter Voltage



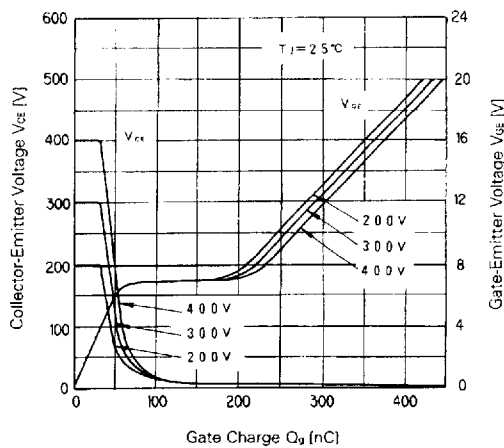
Collector-Emitter Voltage vs. Gate-Emitter Voltage



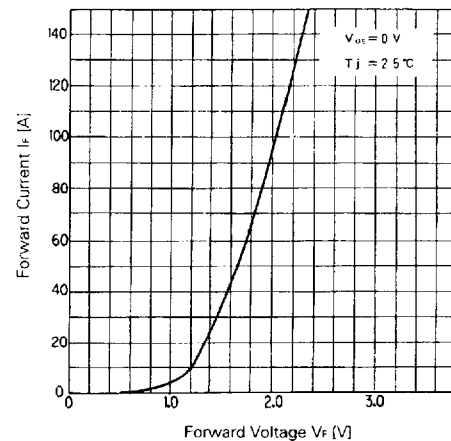
Switching Time



Switching Time-Gate Resistance



Dynamic Input Characteristic



Forward Voltage of Free Wheel Diode

